



报告人： Dr. Naoto Fujishima, the Chief Expert of Development Division in the Electronic Devices Business Group in Fuji Electric

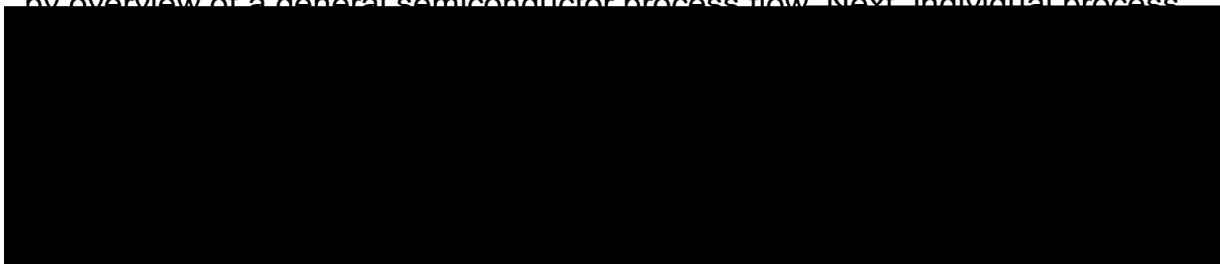
报告时间： 9:00am to 12:00am on June 25th, 2019

报告地点： 电机楼 408

报告内容： Process Technologies for Power Devices (半导体工艺制备技术系列讲座之一)

Abstract

This lecture will focus on process technologies which is used for providing power semiconductor devices. As introduction, power electronics supported by power devices are introduced as the key technologies for realizing sustainable societies. Then feature of power devices is compared with one for LSI, followed by overview of a general semiconductor process flow. Next, individual process



Biography of Speaker

Dr. Naoto Fujishima received B.S. degree in Electronic Engineering from Hokkaido University, Japan, in 1985. After the graduation, he joined Fuji Electric Hokkaido University, Japan, in 1985. After the graduation, he was in charge of R&D on power ICs and design of power device both from the received M.S. and Ph.D. degrees in 1998 and 2003, respectively, by York University and University of Toronto, Canada. He is currently Chief Expert of Development Division in the Electronic Devices Business Group in Fuji Electric. His current responsibilities include development of silicon and silicon carbide power-devices. Dr. Fujishima is a board member of RCM, AIEEA member of SPSO.

欢迎同学们参加!

电气学院